



Italian Distributor



info.sisram@sisram.it - www.sisram.it

SemiSouth **SiC power JFETs & Schottky barrier Diodes** deliver record breaking efficiency, greater power density and higher reliability than comparable Silicon-based or SiC-based devices.

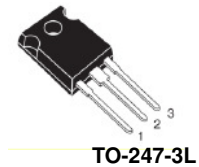


- Features :**
- Low gate charge
 - Low conduction loss
 - Low switching loss
 - High switching frequency
 - High thermal performance

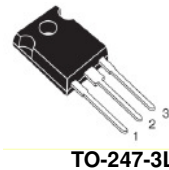
- Applications :**
- Solar Inverter
 - Switch Mode Power Supply
 - Power Factor Correction
 - Induction Heating
 - UPS
 - Motor Drive

Products Range :

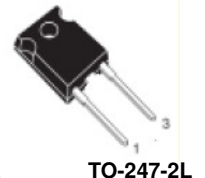
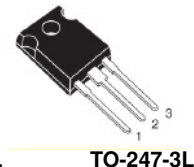
1200 V – 1700 V Trench “normally – off” JFETs 550mΩ to 50mΩ



1200 V Trench “normally – on” JFETs 85mΩ to 45mΩ



1200 V Schottky Diodes 5A to 60A

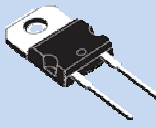
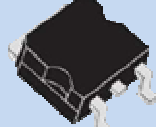
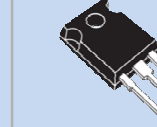
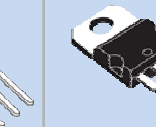
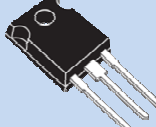
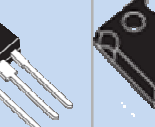
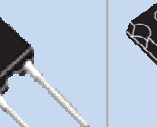


Gate Driver





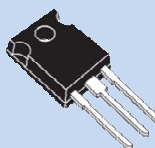
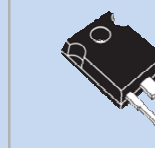
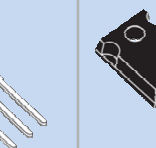
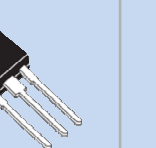

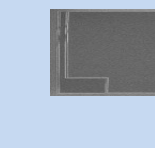
2008-11 SBD Products

Part	SDA05S120	SDB05S120	SDP10S120D	SDA10S120	SDP20S120D	SDP30S120	SDP60S120D
Package	 2L TO-220	 DPAK 2L (TO-252)	 3L TO-247	 2L TO-220	 3L TO-247	 2L TO-247	 3L TO-247
BV (V)	1200	1200	1200	1200	1200	1200	1200
I _F (A)	5A	5A	10A (2 x 5A)	10A	20A (2 x 10A)	30A	60A (2 x 30A)
Samples	2008	Now	2008	2008	2008	2009	Now
Production	2008	EQ2/2011	2008	2008	2008	2009	EQ3/2011

2008-11 Vertical JFET Products

Normally-ON

Normally-OFF

Part	SJDP120R085	SJDP120R045	SJEP120R100	SJEP120R063	SJEC120R050	SJEP170R550
Package	 3L TO-247	 3L TO-247	 3L TO-247	 3L TO-247	 Bare Die Only	 3L TO-247
Voltage	1200 V	1200 V	1200 V	1200 V	1200 V	1700V
R _{ds(on)}	85 mΩ	45 mΩ	100 mΩ	63 mΩ	50 mΩ	550 mΩ
Samples	2009	2011	2008	2009	2010	2009
Production	2009	Q3/2011	2008	2009	Q2/2011	2009

Latest Datasheets at <http://www.semisouth.com/products/products.html>